

## Supporting Information

# Economically Detaching Transparent and Flexible (Al,Ga)N Nanowire Films with Improved Photoelectric Response in view of Ultraviolet Photodetectors

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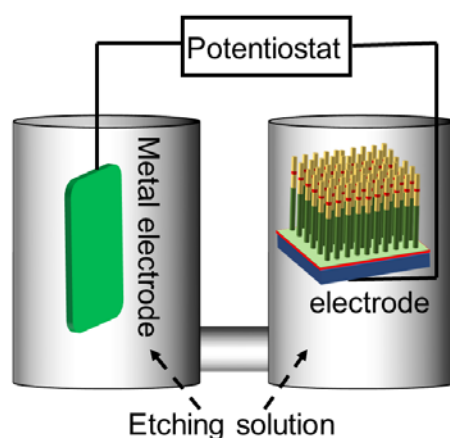


Fig. S1 Schematic illustration of the experimental setup for electrochemical etching.

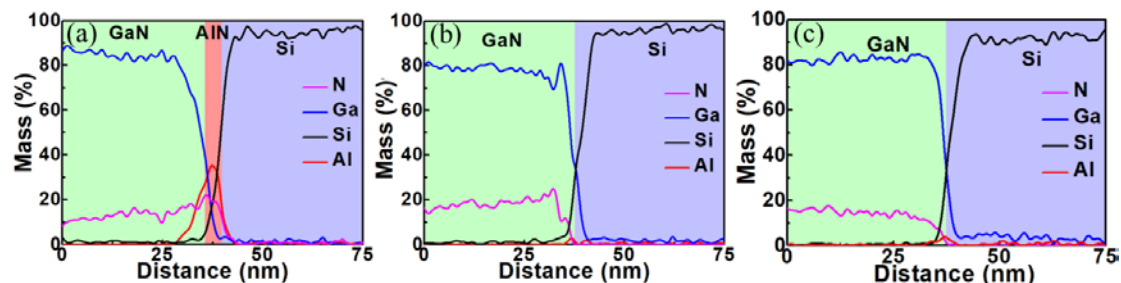


Fig. S2 EDX spectra revealing the element distributions along the interface layers from the NWs to substrates for (a) sample A, (b) sample B (on a foreign Si) and (c) sample C (on a foreign Si).

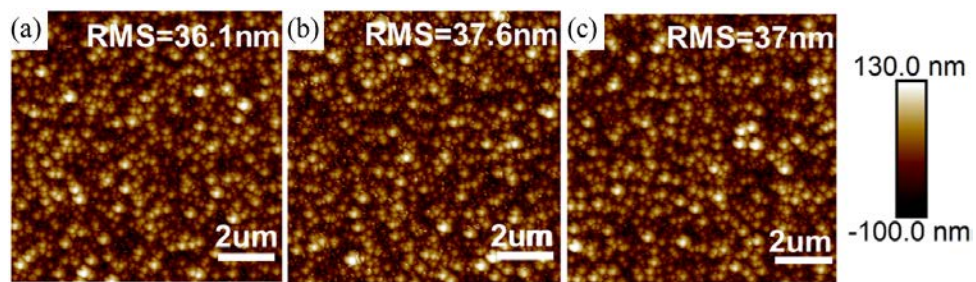


Fig. S3 AFM images of the top NWs of (a) sample A, (b) sample B (on a foreign Si) and (c) sample C (on a foreign Si).